ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE131 (PNP) & NTE155 (NPN)
Germanium Complementary Transistors
Audio Power Amplifier

Description:

The NTE131 (PNP) and NTE155 (NPN) are Germanium PNP Alloy Junction transistors in a Japanese TO66 type package designed for use in audio power amplifier applications.

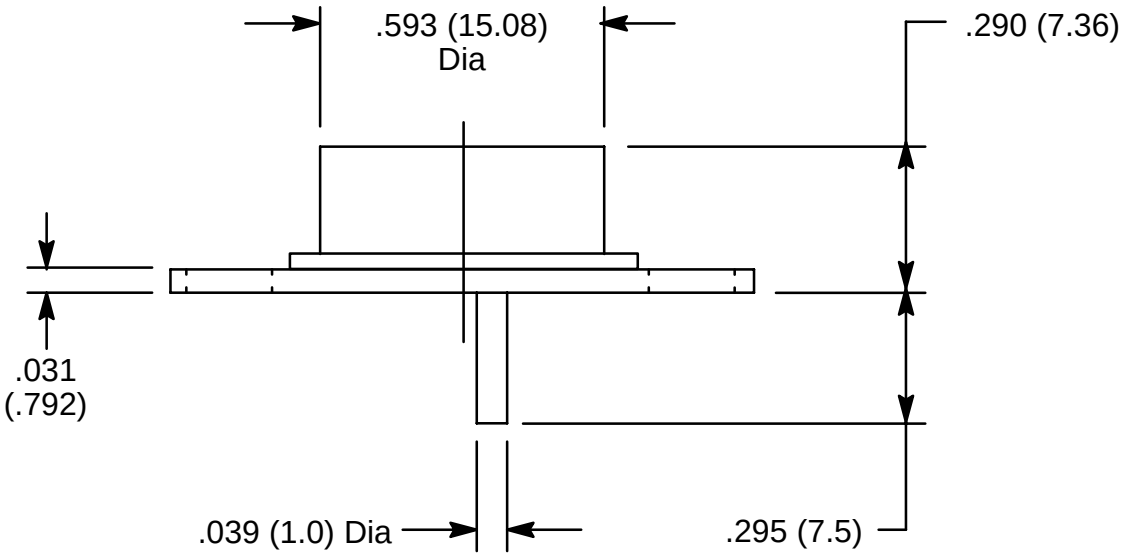
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

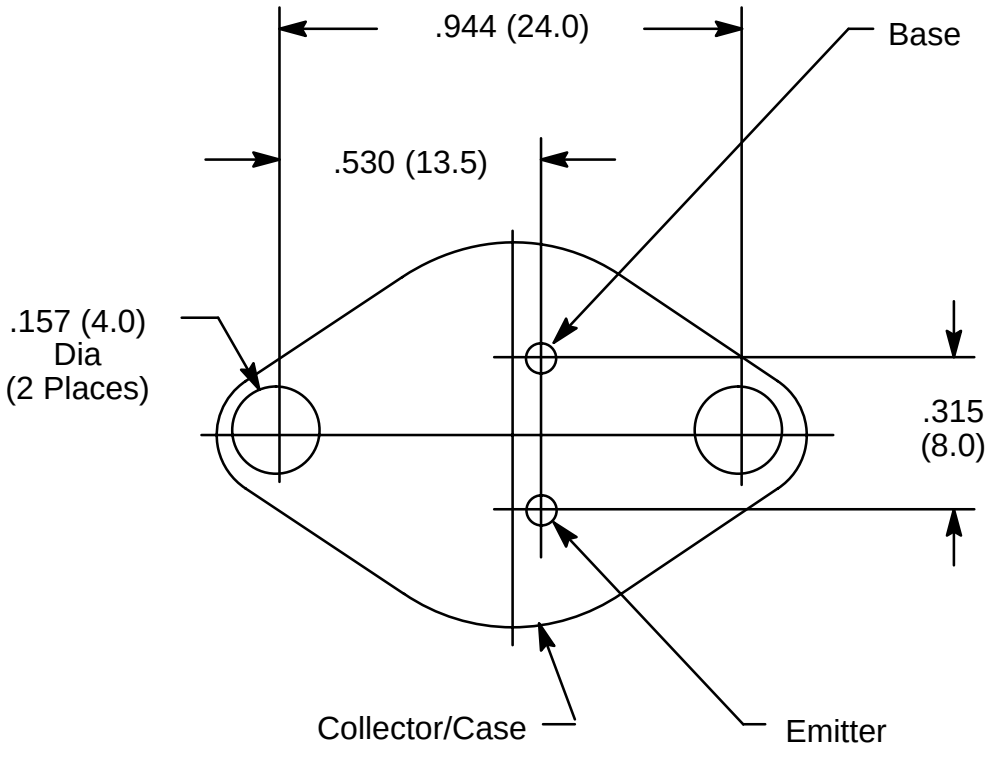
Collector–Base Voltage, V_{CBO} 32V
Collector–Emitter Voltage, V_{CES} 32V
Emitter–Base Voltage, V_{EBO} 10V
Collector Current, I_C 1A
Base Current, I_B 200mA
Power Dissipation, P_C 6W
Operating Junction Temperature, T_J . . . . . +90°C
Storage Temperature Range, T_{stg} . . . . . –55° to +90°C

Note 1. NTE131MP is a matched pair of NTE131 with their DC Current Gain (h_{FE}) matched to within 10% of each other.

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CEV}	V_{CE} = 32V, V_{EB} = 1V	–	–	1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 10V, I_C = 0	–	–	1	mA
DC Current Gain	h_{FE1}	V_{CB} = 0, I_E = 100mA	35	–	170	
	h_{FE2}	V_{CB} = 0, I_E = 1A	36	–	185	
Common–Emitter Cutoff Frequency	$f_{\alpha e}$	V_{CB} = 2V, I_E = 100mA	10	15	–	kHz
Base–Emitter ON Voltage	V_{BE}	V_{CB} = 0, I_E = 1A	–	0.4	–	V
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 1A, I_B = 100mA	–	0.08	–	V


.593 (15.08)
Dia
.290 (7.36)
.031
(.792)
.039 (1.0) Dia
.295 (7.5)


.944 (24.0)
Base
.530 (13.5)
.157 (4.0)
Dia
(2 Places)
.315
(8.0)
Collector/Case
Emitter